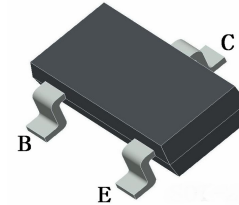


TRANSISTOR (PNP)

FEATURE

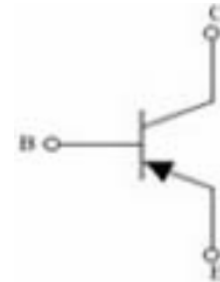
- Complementary to S9014

SOT-23



MARKING: M6

Equivalent Circuit



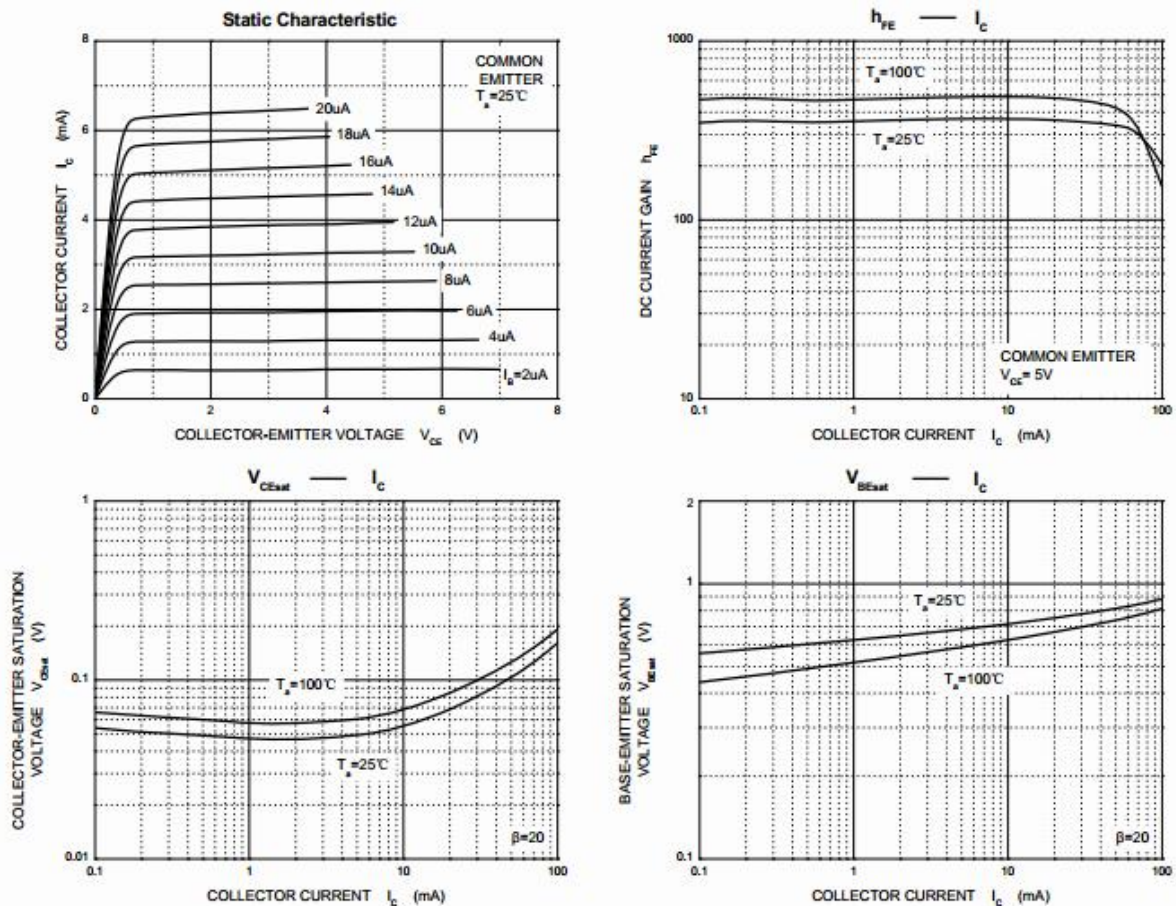
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _{CM}	Collector Current	-0.1	A
P _D	Power Dissipation	0.45	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

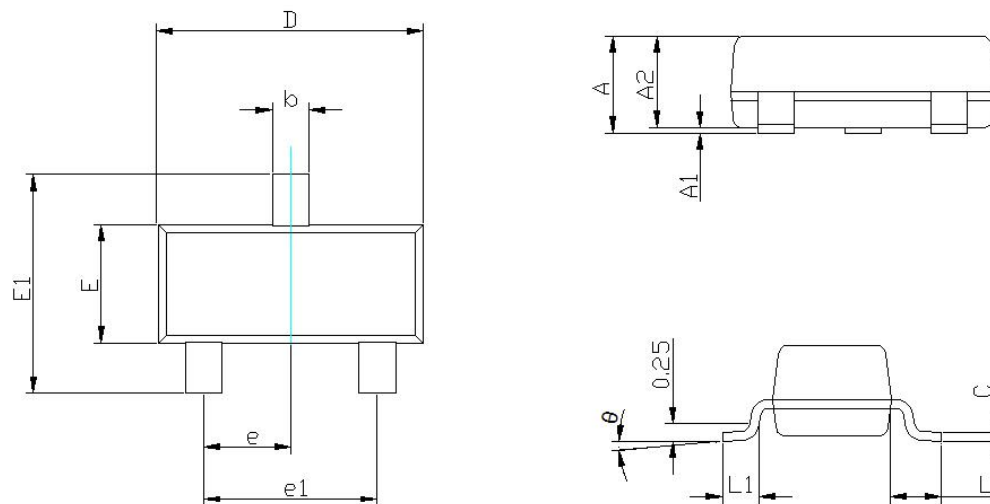
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Max	Unit
BV_{EBO}	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}$, $I_C=0$	-5		V
BV_{CBO}	Collector-base breakdown voltage	$I_C=-100\mu\text{A}$, $I_E=0$	-50		V
BV_{CEO}	Collector-emitter breakdown voltage	$I_C=-100\mu\text{A}$, $I_B=0$	-45		V
I_{EBO}	Emitter cut-off current	$V_{EB}=-5\text{V}$, $I_C=0$		-0.1	μA
I_{CBO}	Collector cut-off current	$V_{CB}=-50\text{V}$, $I_E=0$		-0.1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-45\text{V}$, $I_B=0$		-0.1	μA
$V_{CE_{SAT}}$	Collector-emitter saturation voltage	$I_C=-100\text{mA}$, $I_B=-5\text{mA}$		-0.3	V
$V_{BE_{SAT}}$	Base-emitter saturation voltage	$I_C=-100\text{mA}$, $I_B=-5\text{mA}$		-1.1	V
hfe	DC current gain	$V_{CE}=-5\text{V}$, $I_C=-1\text{mA}$	300	400	
f_T	Transition frequency	$V_{CE}=-5\text{V}$, $I_C=-10\text{mA}$ F=30MHZ	150		MHZ

Typical Characteristics



SOT-23 Package Outline Dimensions



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.15	0.035	0.045
A1	0.000	0.125	0.000	0.005
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF (0.4-0.6)		0.022REF (0.016-0.024)	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°